NSN 5962-01-135-5706

Memory Microcircuit - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5962-01-135-5706
Body Length:
Between 0.870 inches and 0.920 inches
Body Width:
Between 0.280 inches and 0.310 inches
Body Height:
Between 0.130 inches and 0.200 inches
Operating Tempurature Range:
+0.0/+70.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and bipolar and high speed and programmable and schottky
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
12 input
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
7.0 volts power source
Time Rating Per Chacteristic:
25.00 nanoseconds propagation delay time, low to high level output and 25.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Rom
Memory Capacity:
Unknown
Test Data Document:
98747-8071825 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.;
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
18 printed circuit
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:

Fiig: A458a0

Yes - demil/mli